

Sheng-Po Chang

List of Publications by Year in descending order

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195
papers

2,967
citations

159585

30
h-index

214800

47
g-index

195
all docs

195
docs citations

195
times ranked

3495
citing authors

#	ARTICLE	IF	CITATIONS
1	Improved performance of flexible citrus resistive memory device through air plasma. Flexible and Printed Electronics, 2022, 7, 015008.	2.7	0
2	Bright CsPbBr ₃ Perovskite Nanocrystals with Improved Stability by In-Situ Zn-Doping. Nanomaterials, 2022, 12, 759.	4.1	10
3	Silver-Doped Citrus Pectin Resistive Random Access Memory with Multilevel Characteristics. ECS Journal of Solid State Science and Technology, 2022, 11, 055003.	1.8	1
4	AlGaN-Based Deep Ultraviolet Light-Emitting Diodes with Thermally Oxidized Al _x Ga ₂ O ₃ Sidewalls. ACS Omega, 2022, 7, 15027-15036.	3.5	4
5	High Stability Flexible Deep-UV Detector Based on All-Oxide Heteroepitaxial Junction. ACS Applied Electronic Materials, 2022, 4, 3099-3106.	4.3	9
6	The Characteristics of Aluminum-Gallium-Zinc-Oxide Ultraviolet Phototransistors by Co-Sputtering Method. Electronics (Switzerland), 2021, 10, 631.	3.1	2
7	Stability-Enhanced Resistive Random-Access Memory via Stacked In _x Ga _{1-x} O by the RF Sputtering Method. ACS Omega, 2021, 6, 10691-10697.	3.5	4
8	Investigating the Photodetectors and pH Sensors of Two-Dimensional MoS ₂ with Different Substrates. ECS Journal of Solid State Science and Technology, 2021, 10, 055015.	1.8	0
9	Investigation of MgIn ₂ O ₄ MSM UV Photodetector With Different Oxygen Flow Ratios and Post-Annealing Temperatures. ECS Journal of Solid State Science and Technology, 2021, 10, 055014.	1.8	2
10	Switching Properties Improvement of Tungsten-Doped Indium Oxide Phototransistor. ECS Journal of Solid State Science and Technology, 2021, 10, 075007.	1.8	0
11	Development of Indium Titanium Zinc Oxide Thin Films Used as Sensing Layer in Gas Sensor Applications. Coatings, 2021, 11, 807.	2.6	5
12	Fabrication and Characterization of In _{0.9} Ga _{0.1} O EGFET pH Sensors. Coatings, 2021, 11, 929.	2.6	3
13	High Response of Ethanol Gas Sensor Based on NiO-Doped Apple Pectin by the Solution Process. Coatings, 2021, 11, 1073.	2.6	1
14	Deep Ultraviolet AlGaN-Based Light-Emitting Diodes with p-AlGaN/AlGaN Superlattice Hole Injection Structures. Processes, 2021, 9, 1727.	2.8	3
15	Performance Improvement of Co-Sputtering AlGaZnO Solar-Blind Photodetectors. IEEE Sensors Journal, 2021, 21, 18682-18687.	4.7	2
16	Indium Aluminum Zinc Oxide Phototransistor With HfO ₂ Dielectric Layer Through Atomic Layer Deposition. IEEE Sensors Journal, 2020, 20, 1838-1842.	4.7	3
17	MgZnO/SiO ₂ /ZnO metal-semiconductor-metal dual-band UVA and UVB photodetector with different MgZnO thicknesses by RF magnetron sputter. Japanese Journal of Applied Physics, 2020, 59, SDDF04.	1.5	9
18	Photoresponses of Zinc Tin Oxide Thin-Film Transistor. Journal of Nanoscience and Nanotechnology, 2020, 20, 1704-1708.	0.9	7

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19	Voltage-Tunable UV-Visible Dual-Band Metal-Semiconductor Metal Photodetector Based on Ga ₂ O ₃ /MgZnO Heterostructure by RF Sputtering. <i>Coatings</i> , 2020, 10, 994.	2.6	6
20	Characteristics of MgIn ₂ O ₄ Thin Film Transistors Enhanced by Introducing an MgO Buffer Layer. <i>Coatings</i> , 2020, 10, 1261.	2.6	0
21	Investigation of Conductive Mechanism of Amorphous IGO Resistive Random-Access Memory with Different Top Electrode Metal. <i>Coatings</i> , 2020, 10, 504.	2.6	4
22	An Amorphous (Al _{0.12} Ga _{0.88}) ₂ O ₃ Deep Ultraviolet Photodetector. <i>IEEE Photonics Journal</i> , 2020, 12, 1-8.	2.0	2
23	Polycrystalline InGaO Thin-Film Transistors Coupled With a Nitrogen Doping Technique for High-Performance UV Detectors. <i>IEEE Transactions on Electron Devices</i> , 2020, 67, 140-145.	3.0	3
24	Ambient-Processed, Additive-Assisted CsPbBr ₃ Perovskite Light-Emitting Diodes with Colloidal NiOx Nanoparticles for Efficient Hole Transporting. <i>Coatings</i> , 2020, 10, 336.	2.6	10
25	AlGaN-based deep ultraviolet light emitting diodes with magnesium delta-doped AlGaN last barrier. <i>Applied Physics Letters</i> , 2020, 117, .	3.3	17
26	MgZnO MSM UV Photodetector with Different Annealing Temperatures by RF Magnetron Sputtering. <i>ECS Journal of Solid State Science and Technology</i> , 2020, 9, 055015.	1.8	1
27	Investigation of nitrogen doping effects on light-induced oxygen vacancy ionization and oxygen desorption in c-IGO TFTs. <i>Materials Research Express</i> , 2019, 6, 106445.	1.6	3
28	Ultraviolet/Visible Photodetectors Based on NiO/ZnO Nanowires Decorated with Pd Nanoparticles. <i>ACS Applied Nano Materials</i> , 2019, 2, 6343-6351.	5.0	36
29	Effect of oxygen vacancy concentration on indium tungsten oxide UV-A photodetector. <i>RSC Advances</i> , 2019, 9, 87-90.	3.6	7
30	The Effect of Oxygen Partial Pressure and Annealing Process on the Characteristics of ZnGa ₂ O ₄ MSM UV Photodetector. <i>ECS Journal of Solid State Science and Technology</i> , 2019, 8, Q3213-Q3216.	1.8	19
31	Integration of bandgap-engineered double-stacked channel layers with nitrogen doping for high-performance InGaO TFTs. <i>Applied Physics Letters</i> , 2019, 114, .	3.3	20
32	Indium Aluminum Zinc Oxide Thin Film Transistor With Al ₂ O ₃ Dielectric for UV Sensing. <i>IEEE Photonics Technology Letters</i> , 2019, 31, 1005-1008.	2.5	7
33	Indium Gallium Oxide Thin Film Transistor for Two-Stage UV Sensor Application. <i>ECS Journal of Solid State Science and Technology</i> , 2019, 8, Q3140-Q3143.	1.8	15
34	Stability Improvement of Nitrogen Doping on IGO TFTs under Positive Gate Bias Stress and Hysteresis Test. <i>ECS Journal of Solid State Science and Technology</i> , 2019, 8, Q3034-Q3040.	1.8	10
35	Solution-Processed UV and Visible Photodetectors Based on Y-Doped ZnO Nanowires with TiO ₂ Nanosheets and Au Nanoparticles. <i>ACS Applied Energy Materials</i> , 2018, 1, 2087-2095.	5.1	48
36	Bandgap Engineered Ultraviolet Photodetectors with Gallium-Zinc-Oxide via Co-Sputtering Method. <i>ECS Journal of Solid State Science and Technology</i> , 2018, 7, Q3083-Q3088.	1.8	6

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37	Amorphous Indium Titanium Zinc Oxide Thin Film Transistor and Impact of Gate Dielectrics on Its Photo-Electrical Properties. ECS Journal of Solid State Science and Technology, 2018, 7, Q3049-Q3053.	1.8	3
38	Photo-Electrical Properties of MgZnO Thin-Film Transistors With High- ϵ Dielectrics. IEEE Photonics Technology Letters, 2018, 30, 59-62.	2.5	17
39	Influence of oxygen on the performance of indium titanium zinc oxide UV sensors fabricated via RF sputtering. Materials Science in Semiconductor Processing, 2018, 74, 297-302.	4.0	8
40	Photoresponses of Gallium Zinc Tin Oxide Thin-Film Transistors Fabricated by Cosputtering Method. , 2018, 2, 1-4.		1
41	Growth and Crystal Structure Investigation of InAs/GaSb Heterostructure Nanowires on Si Substrate. IEEE Nanotechnology Magazine, 2018, 17, 1151-1158.	2.0	4
42	Effect of Oxygen Vacancy Ratio on a GaZTO Solar-Blind Photodetector. Coatings, 2018, 8, 293.	2.6	14
43	Electrical Properties of Indium Aluminum Zinc Oxide Thin Film Transistors. Journal of Electronic Materials, 2018, 47, 6923-6928.	2.2	17
44	Highly Stable Ultrathin TiO ₂ Based Resistive Random Access Memory with Low Operation Voltage. ECS Journal of Solid State Science and Technology, 2018, 7, Q3183-Q3188.	1.8	24
45	Highly stable ITO/Zn ₂ TiO ₄ /Pt resistive random access memory and its application in two-bit-per-cell. RSC Advances, 2018, 8, 17622-17628.	3.6	12
46	Bandgap-Engineered Zinc-Tin-Oxide Thin Films for Ultraviolet Sensors. Journal of Nanoscience and Nanotechnology, 2018, 18, 4930-4934.	0.9	3
47	Optical and photo-electrical properties of zinc tin oxide thin-film phototransistor. , 2018, , .		2
48	Effect of different partial pressure on Ga-doped ZnO UV photodetectors by RF sputtering. , 2018, , .		0
49	Communicationâ€”Diffusion Break-Assisted Programming Mode for Active Electrically Programmable Fuse. ECS Journal of Solid State Science and Technology, 2018, 7, Q109-Q111.	1.8	3
50	Doping Nitrogen in InGaZnO Thin Film Transistor with Double Layer Channel Structure. Journal of Nanoscience and Nanotechnology, 2018, 18, 2493-2497.	0.9	3
51	Fabrication of Zinc Oxide-Based Thin-Film Transistors by Radio Frequency Sputtering for Ultraviolet Sensing Applications. Journal of Nanoscience and Nanotechnology, 2018, 18, 3518-3522.	0.9	5
52	Properties of Gaâ€”Znâ€”O Ultraviolet Phototransistors Using Radio-Frequency Magnetron Co-Sputtering Method. Nanoscience and Nanotechnology Letters, 2018, 10, 396-402.	0.4	1
53	Suppression of electron overflow in 370-nm InGaN/AlGaIn ultraviolet light emitting diodes with different insertion layer thicknesses. Journal of Crystal Growth, 2017, 468, 585-589.	1.5	1
54	Influence of Annealing Ambience on TiO ₂ Film Ultraviolet Photodetector. ECS Journal of Solid State Science and Technology, 2017, 6, Q3056-Q3060.	1.8	5

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55	Transparent gas sensor and photodetector based on Al doped ZnO nanowires synthesized on glass substrate. <i>Ceramics International</i> , 2017, 43, 5434-5440.	4.8	36
56	Tunable UV- and Visible-Light Photoresponse Based on p-ZnO Nanostructures/n-ZnO/Glass Peppered with Au Nanoparticles. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 14935-14944.	8.0	57
57	High Responsivity Indium-Zinc-Oxide Ultraviolet Thin-Film Phototransistor. <i>Journal of Nanoscience and Nanotechnology</i> , 2017, 17, 4864-4866.	0.9	3
58	Performance improvement of highly mismatched GaSb layers on GaAs by interfacial-treatment-assisted chemical vapor deposition. <i>Journal of Materials Science: Materials in Electronics</i> , 2017, 28, 845-855.	2.2	0
59	Optical Switch of a-IGZO TFT and Triple Junction Photovoltaic Cell. <i>ECS Journal of Solid State Science and Technology</i> , 2017, 6, Q120-Q122.	1.8	2
60	GaN-Based Blue Light-Emitting Diodes with an Electron Transmission Layer. <i>ECS Journal of Solid State Science and Technology</i> , 2017, 6, R154-R157.	1.8	4
61	Efficiency Enhancement in InGaN Photovoltaic Cells With Inverted Textured Surface. <i>IEEE Photonics Technology Letters</i> , 2017, 29, 1304-1307.	2.5	1
62	Suppressing efficiency droop using graded AlGaIn/InGaIn superlattice electron blocking layer for InGaIn-based light-emitting diodes. <i>Journal of Crystal Growth</i> , 2017, 468, 562-566.	1.5	4
63	High Responsivity MgZnO Ultraviolet Thin-Film Phototransistor Developed Using Radio Frequency Sputtering. <i>Materials</i> , 2017, 10, 126.	2.9	23
64	Oxygen Partial Pressure Impact on Characteristics of Indium Titanium Zinc Oxide Thin Film Transistor Fabricated via RF Sputtering. <i>Nanomaterials</i> , 2017, 7, 156.	4.1	15
65	The Effect of the Thickness and Oxygen Ratio Control of Radio-Frequency Magnetron Sputtering on MgZnO Thin-Film Transistors. <i>Journal of Nanoscience and Nanotechnology</i> , 2017, 17, 2037-2040.	0.9	1
66	The Influence of Different Partial Pressure on the Fabrication of InGaO Ultraviolet Photodetectors. <i>Sensors</i> , 2016, 16, 2145.	3.8	14
67	Investigation of the effect of nitride-based LEDs fabricated using hole injection layer at different growth temperatures. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 05FJ14.	1.5	0
68	Growth of ultrathin GaSb layer on GaAs using metal-organic chemical vapor deposition with Sb interfacial treatment. <i>Applied Physics Express</i> , 2016, 9, 095502.	2.4	5
69	Performance Enhancement of Blue InGaIn Light-Emitting Diodes with P-GaN/InGaIn SPS Last Barrier and P-AlGaIn/GaN SPS EBL. <i>ECS Journal of Solid State Science and Technology</i> , 2016, 5, Q179-Q182.	1.8	4
70	Characterization of High Mg Content MgZnO Ultraviolet Photodetectors with Noise Properties. <i>ECS Journal of Solid State Science and Technology</i> , 2016, 5, Q191-Q194.	1.8	6
71	High Responsivity Mg _x Zn _{1-x} O Film UV Photodetector Grown by RF Sputtering. <i>IEEE Photonics Technology Letters</i> , 2015, 27, 978-981.	2.5	18
72	Scalability of Phase Change Materials in Nanostructure Template. <i>International Journal of Photoenergy</i> , 2015, 2015, 1-4.	2.5	0

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73	New Energy Materials and Device Application. International Journal of Photoenergy, 2015, 2015, 1-1.	2.5	0
74	Photoelectrochemical characterization of n-type and p-type thin-film nanocrystalline Cu ₂ ZnSnSe ₄ photocathodes. Journal of Environmental Chemical Engineering, 2015, 3, 297-303.	6.7	25
75	GaN MSM UV Photodetector With Sputtered AlN Nucleation Layer. IEEE Sensors Journal, 2015, 15, 4743-4748.	4.7	37
76	A Novel pH Sensor Using Extended-Gate Field-Effect Transistors with Ga ₂ O ₃ Nanowires Fabricated on SiO ₂ /Si Template. Science of Advanced Materials, 2015, 7, 475-478.	0.7	8
77	Concepts of Novel Nanomaterial Device and Application. Journal of Nanomaterials, 2014, 2014, 1-1.	2.7	0
78	Electrical Properties of Amorphous Zinc-Indium-Tin Oxide Semiconductor Thin-Film Transistors. Nanoscience and Nanotechnology Letters, 2014, 6, 273-278.	0.4	1
79	Beta-Gallium Oxide Nanowire Extended Gate Field Effect Transistor pH Sensors Prepared Using Furnace-Oxidized Gallium Nitride Thin Films. Nanoscience and Nanotechnology Letters, 2014, 6, 914-917.	0.4	8
80	Sensitivity of EGFET pH Sensors with TiO ₂ Nanowires. ECS Solid State Letters, 2014, 3, P123-P126.	1.4	35
81	Investigation of zinc-tin-oxide thin-film transistors with varying SnO ₂ contents. Electronic Materials Letters, 2014, 10, 89-94.	2.2	8
82	Two-dimensional ZnO nanowalls for gas sensor and photoelectrochemical applications. Electronic Materials Letters, 2014, 10, 693-697.	2.2	14
83	See-Through Si Thin-Film Tandem Solar Cell Module With Hardener. IEEE Journal of Photovoltaics, 2014, 4, 1013-1017.	2.5	3
84	Performance Enhancement of High-Current-Injected Electrically Programmable Fuse With Compressive-Stress Nitride Layer. IEEE Electron Device Letters, 2014, 35, 297-299.	3.9	4
85	Amorphous InGaZnO Ultraviolet Phototransistors With a Thin Ga ₂ O ₃ Layer. IEEE Journal of Selected Topics in Quantum Electronics, 2014, 20, 125-129.	2.9	14
86	Synthesis of CZTSe nanoink via a facile one-pot heating route based on polyetheramine chelation. Solar Energy Materials and Solar Cells, 2014, 128, 156-165.	6.2	18
87	The Cu Concentration Effect on the Electro-Optical Properties of Cu ₂ ZnSnSe ₄ Thin Films Prepared by a Non-Vacuum Solution-Based Nano-Inks Process. Science of Advanced Materials, 2014, 6, 18-26.	0.7	0
88	Amorphous Indium-Zinc Oxide Semiconductor Thin-Film Transistors. Journal of Nanoelectronics and Optoelectronics, 2014, 9, 388-391.	0.5	0
89	Noise Properties of ZnO Nanowalls Deposited Using Rapid Thermal Evaporation Technology. IEEE Photonics Technology Letters, 2013, 25, 213-216.	2.5	7
90	Triple-Junction GaInP/GaAs/Ge Solar Cells With an AZO Transparent Electrode and ZnO Nanowires. IEEE Journal of Photovoltaics, 2013, 3, 991-996.	2.5	12

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91	Method for Improving the Stability of Gen 5 Silicon Thin-film Tandem Solar Cell. IEEE Journal of Photovoltaics, 2013, 3, 1140-1143.	2.5	1
92	Investigating the Effect of Piezoelectric Polarization on GaN-Based LEDs With Different Quantum Barrier Thickness. Journal of Display Technology, 2013, 9, 206-211.	1.2	14
93	Synthesis of Cu ₂ ZnSnSe ₄ nanocrystals from metal sources using a facile process in isophorondiamine. Materials Letters, 2013, 98, 71-73.	2.6	10
94	Effect of surface modification by self-assembled monolayer on the ZnO film ultraviolet sensor. Applied Physics Letters, 2013, 103, 022101.	3.3	6
95	Fabrication and Photoelectrochemical Behavior of n-Type Cu ₂ ZnSnSe ₄ Thin-Film Electrodes Prepared via Non-Vacuum Nanoinks Process. ECS Journal of Solid State Science and Technology, 2013, 2, Q220-Q223.	1.8	8
96	Optoelectronic Properties of Thermally Evaporated ZnO Films with Nanowalls on Glass Substrates. Applied Physics Express, 2013, 6, 045201.	2.4	3
97	The inter-metallic oxide of ZnO/ITO/ZnO tri-layer films using a heat-induced diffusion mechanism. Applied Surface Science, 2013, 273, 598-602.	6.1	6
98	Efficiency of GaN/InGaN double-heterojunction photovoltaic cells under concentrated illumination. Surface and Coatings Technology, 2013, 231, 253-256.	4.8	10
99	Improved efficiency of p-type quasi-mono silicon blanket emitter solar cell by ion implantation and backside rounding. Materials Science-Poland, 2013, 31, 516-524.	1.0	0
100	Simple Fabrication Process for 2D ZnO Nanowalls and Their Potential Application as a Methane Sensor. Sensors, 2013, 13, 3941-3950.	3.8	52
101	p-Type Quasi-Mono Silicon Solar Cell Fabricated by Ion Implantation. International Journal of Photoenergy, 2013, 2013, 1-8.	2.5	3
102	Low Cost Amorphous Silicon Intrinsic Layer for Thin-Film Tandem Solar Cells. International Journal of Photoenergy, 2013, 2013, 1-5.	2.5	0
103	Fabrication of Simple GaAs Solar Cell by Zn Diffusion Method. Advanced Materials Research, 2013, 684, 312-316.	0.3	3
104	Fabrication of ZnO Nanowall-Based Hydrogen Gas Nanosensor. Advanced Materials Research, 2013, 684, 21-25.	0.3	4
105	Synchrotron radiation based cross-sectional scanning photoelectron microscopy and spectroscopy of n-ZnO:Al/p-GaN:Mg heterojunction. Applied Physics Letters, 2013, 102, .	3.3	6
106	Reducing the Current Crowding Effect on Nitride-Based Light-Emitting Diodes Using Modulated P-Extension Electrode Thickness. Japanese Journal of Applied Physics, 2013, 52, 01AG05.	1.5	2
107	Effect of Oxygen Partial Pressure on Electrical Characteristics of Amorphous Indium-Gallium-Zinc-Oxide Thin-Film Transistors. Journal of Nanoelectronics and Optoelectronics, 2013, 8, 361-365.	0.5	1
108	Growth of InN Nanorods on Glass Substrates by Molecular Beam Heteroepitaxy. Science of Advanced Materials, 2013, 5, 873-880.	0.7	2

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109	Influence of Weight Ratio of Poly(4-vinylphenol) Insulator on Electronic Properties of InGaZnO Thin-Film Transistor. Journal of Nanomaterials, 2012, 2012, 1-7.	2.7	10
110	High-Efficiency Si Solar Cell Fabricated by Ion Implantation and Inline Backside Rounding Process. International Journal of Photoenergy, 2012, 2012, 1-7.	2.5	14
111	GaN Schottky Diode with TiW Electrodes on Silicon Substrate Based on AlN/AlGaIn Buffer Layer. Journal of Nanomaterials, 2012, 2012, 1-5.	2.7	0
112	Zinc Oxide Nanoparticle Photodetector. Journal of Nanomaterials, 2012, 2012, 1-5.	2.7	17
113	Amorphous Hafnium-Indium-Zinc Oxide Semiconductor Thin Film Transistors. Journal of Nanomaterials, 2012, 2012, 1-4.	2.7	2
114	Effect of Varied Undoped GaN Thickness on ESD and Optical Properties of GaN-Based LEDs. IEEE Photonics Technology Letters, 2012, 24, 800-802.	2.5	5
115	Characteristics of GaN/InGaIn Double-Heterostructure Photovoltaic Cells. International Journal of Photoenergy, 2012, 2012, 1-5.	2.5	4
116	A Visible-Blind TiO ₂ Nanowire Photodetector. Journal of the Electrochemical Society, 2012, 159, J132-J135.	2.9	41
117	InGaIn-Based Light-Emitting Diodes With an AlGaIn Staircase Electron Blocking Layer. IEEE Photonics Technology Letters, 2012, 24, 1737-1740.	2.5	6
118	Inserting a p-InGaIn layer before the p-AlGaIn electron blocking layer suppresses efficiency droop in InGaIn-based light-emitting diodes. Applied Physics Letters, 2012, 101, 081120.	3.3	35
119	Characteristics of InGaIn-Based Light-Emitting Diodes on Patterned Sapphire Substrates with Various Pattern Heights. Journal of Nanomaterials, 2012, 2012, 1-6.	2.7	9
120	High-performance amorphous indium-gallium-zinc oxide thin-film transistors with polymer gate dielectric. Thin Solid Films, 2012, 520, 5455-5458.	1.8	8
121	ZnO-Nanowire-Based Extended-Gate Field-Effect-Transistor pH Sensors Prepared on Glass Substrate. Science of Advanced Materials, 2012, 4, 1174-1178.	0.7	21
122	UV Illumination Room-Temperature ZnO Nanoparticle Ethanol Gas Sensors. ISRN Nanotechnology, 2012, 2012, 1-5.	1.3	18
123	Growth and Photoelectric Properties of Twinned ZnSe _{1-x} Te _x Nanotips. IEEE Nanotechnology Magazine, 2011, 10, 379-384.	2.0	2
124	ZnSe/ZnCdSeTe Superlattice Nanotips. IEEE Nanotechnology Magazine, 2011, 10, 682-687.	2.0	0
125	Improved Optical and ESD Characteristics for GaN-Based LEDs With an In ⁿ -GaIn Layer. IEEE Transactions on Device and Materials Reliability, 2011, 11, 76-80.	2.0	5
126	Isopropyl Alcohol Sensors of CuO Nanotubes by Thermal Oxidation of Copper Films on Glass. IEEE Sensors Journal, 2011, 11, 3276-3282.	4.7	5

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127	A Deep UV Sensitive $\text{Ta}_2\text{O}_5/\text{a-IGZO}$ TFT. IEEE Sensors Journal, 2011, 11, 2902-2905.	4.7	11
128	CuO-Nanowire Field Emitter Prepared on Glass Substrate. IEEE Nanotechnology Magazine, 2011, 10, 1161-1165.	2.0	16
129	A study on crystallization, optical and electrical properties of the advanced ZITO thin films using co-sputtering system. Journal of Alloys and Compounds, 2011, 509, 3667-3671.	5.5	12
130	Effects of Oxygen Contents in the Active Channel Layer on Electrical Characteristics of IGZO-Based Thin Film Transistors. AIP Conference Proceedings, 2011, , .	0.4	0
131	High-Performance a-IGZO Thin-Film Transistor with Organic Polymer Dielectric Layer. , 2011, , .		3
132	Effect of oxygen partial pressure on electrical characteristics of amorphous indium gallium zinc oxide thin-film transistors fabricated by thermal annealing. Vacuum, 2011, 86, 246-249.	3.5	15
133	Electrical and Optical Characteristics of UV Photodetector With Interlaced ZnO Nanowires. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 990-995.	2.9	45
134	A Novel Fabrication of p-n Diode Based on ZnO Nanowire/p-NiO Heterojunction. Japanese Journal of Applied Physics, 2011, 50, 01AJ05.	1.5	6
135	Hole transport improvement in InGaN/GaN light-emitting diodes by graded-composition multiple quantum barriers. Applied Physics Letters, 2011, 99, .	3.3	123
136	Use of the Thermal Chemical Vapor Deposition to Fabricate Light-Emitting Diodes Based on ZnO Nanowire/p-GaN Heterojunction. Journal of Nanomaterials, 2011, 2011, 1-4.	2.7	2
137	Effect of Silicon Doped Quantum Barriers on Nitride-Based Light Emitting Diodes. Journal of the Electrochemical Society, 2011, 158, H836.	2.9	4
138	Efficiency droop improvement in InGaN/GaN light-emitting diodes by graded-composition electron blocking layer. , 2011, , .		0
139	The comprehensive characteristics of quaternary AlInGaN with various TMI molar rate. Proceedings of SPIE, 2010, , .	0.8	0
140	Quaternary ZnCdSeTe Nanowires. Journal of Nanoscience and Nanotechnology, 2010, 10, 798-802.	0.9	2
141	ZnO Nanowire-Based UV Photodetector. Journal of Nanoscience and Nanotechnology, 2010, 10, 1135-1138.	0.9	5
142	Enhanced field emission of well-aligned ZnO nanowire arrays illuminated by UV. Chemical Physics Letters, 2010, 490, 176-179.	2.6	34
143	Growth of quaternary AlInGaN with various TMI molar rates. Journal of Crystal Growth, 2010, 312, 1920-1924.	1.5	14
144	An investigation of the microstructure, optical and electrical properties of ZITO thin film using the sol-gel method. Journal of Sol-Gel Science and Technology, 2010, 54, 347-354.	2.4	14

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145	A ZnO nanowire-based humidity sensor. Superlattices and Microstructures, 2010, 47, 772-778.	3.1	118
146	Characteristics of efficiency droop in GaN-based light emitting diodes with an insertion layer between the multiple quantum wells and n-GaN layer. Applied Physics Letters, 2010, 97, .	3.3	34
147	Efficiency droop alleviation in InGaN/GaN light-emitting diodes by graded-thickness multiple quantum wells. Applied Physics Letters, 2010, 97, .	3.3	76
148	Laterally Grown n-ZnO Nanowire/p-GaN Heterojunction Light Emitting Diodes. Journal of the Electrochemical Society, 2010, 157, H866.	2.9	6
149	A Lateral ZnO Nanowire Photodetector Prepared on Glass Substrate. Journal of the Electrochemical Society, 2010, 157, K30.	2.9	61
150	Growth of ZnSe[sub 1- λ]Te[sub λ] Nanotips and the Fabrication of ZnSe[sub 1- λ]Te[sub λ] Nanotip-Based Photodetector. Journal of the Electrochemical Society, 2010, 157, K1.	2.9	10
151	Hole injection and efficiency droop improvement in InGaN/GaN light-emitting diodes by band-engineered electron blocking layer. Applied Physics Letters, 2010, 97, 261103.	3.3	190
152	A Solar-Blind β -Ga ₂ O ₃ Nanowire Photodetector. IEEE Photonics Technology Letters, 2010, 22, 709-711.	2.5	47
153	High-Performance a-IGZO Thin-Film Transistor Using Ta_2O_5 Gate Dielectric. IEEE Electron Device Letters, 2010, , .	3.9	56
154	Fabrication of a White-Light-Emitting Diode by Doping Gallium into ZnO Nanowire on a p-GaN Substrate. Journal of Physical Chemistry C, 2010, 114, 12422-12426.	3.1	54
155	10-Gb/s Planar InGaAs P-I-N Photodetectors. IEEE Sensors Journal, 2010, 10, 1559-1563.	4.7	4
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